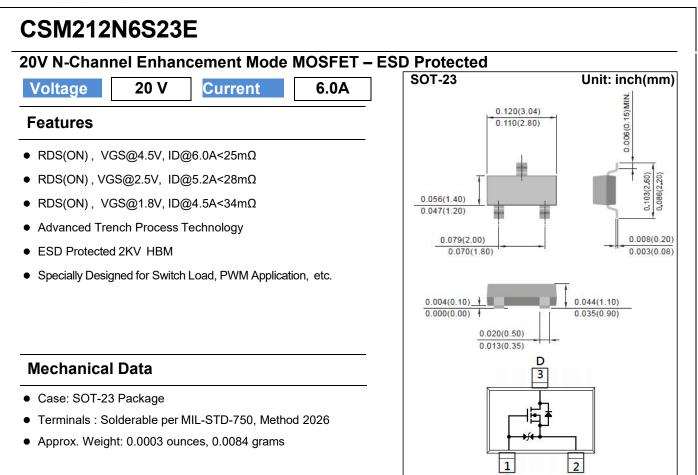
## 



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	20	V
Gate-Source Voltage		V <sub>GS</sub>	±12	V
Continuous Drain Current		ID	6.0	А
Pulsed Drain Current (Note 4)		I <sub>DM</sub>	24.0	А
Power Dissipation	T <sub>a</sub> =25°C	PD	1.25	W
	Derate above 25°C		10	mW/ °C
Operating Junction and Storage Temperature Range		$T_{J}, T_{STG}$	-55~150	°C
Typical Thermal resistance Junction to Ambient <sup>(Note 3)</sup>		R <sub>0JA</sub>	100	°C/W



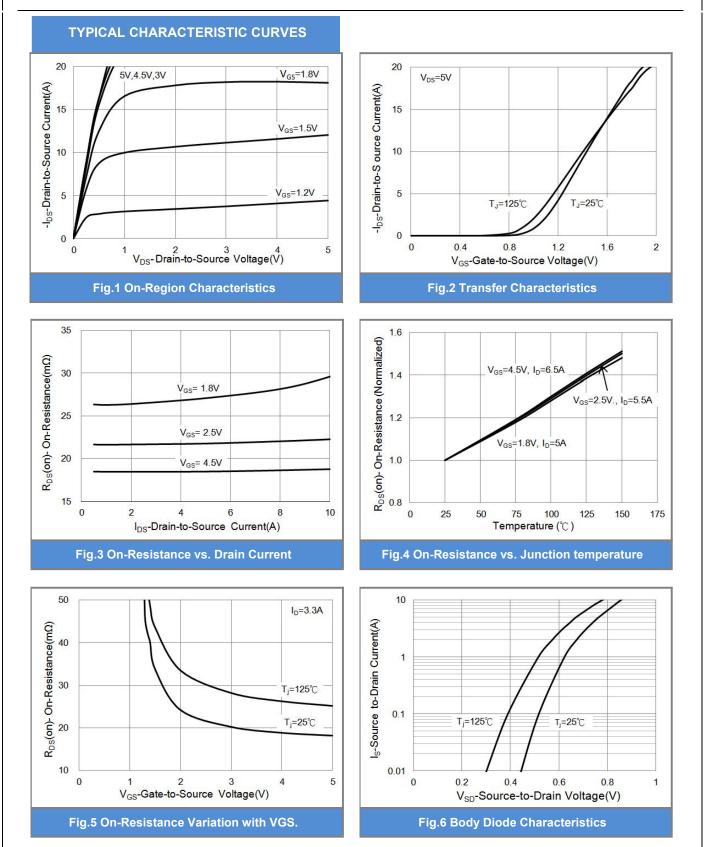
### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static		-				
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}$ =0V, I <sub>D</sub> =250uA	20	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250$ uA	0.4	0.58	1.0	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =6.0A	-	18.4	25	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =5.2A	-	21.5	28	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =4.5A	-	26.4	34	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =20V, $V_{GS}$ =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 8V, V <sub>DS</sub> =0V	-	-	<u>+</u> 10	uA
Dynamic						
Total Gate Charge	Qg	- V <sub>DS</sub> =10V, I <sub>D</sub> =6.0A, - V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	8.6	-	nC
Gate-Source Charge	$Q_gs$		-	1.06	-	
Gate-Drain Charge	$Q_{gd}$		-	1.04	-	
Input Capacitance	Ciss	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V,	-	836	-	pF
Output Capacitance	Coss		-	96	-	
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	80	-	
Switching						
Turn-On Delay Time	td <sub>(on)</sub>		-	24	-	ns
Turn-On Rise Time	tr	$V_{DD}$ =10V, I <sub>D</sub> =1A, V <sub>GS</sub> =4.5V, R <sub>G</sub> =3Ω <sup>(Note 1,2)</sup>	-	46	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	0.22	-	us
Turn-Off Fall Time	tf	$R_{G}=3\Omega$	-	0.30	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	ls		-	-	1.5	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V	-	0.74	1.0	V

NOTES :

- 1. Pulse width300us, Duty cycle<2%</td>
- 2. Essentially independent of operating temperature typical characteristics.
- 3.  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.







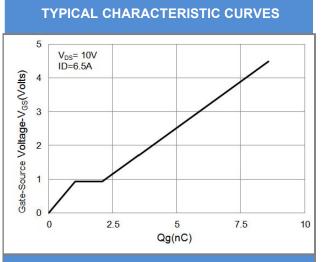


Fig.7 Gate-Charge Characteristics

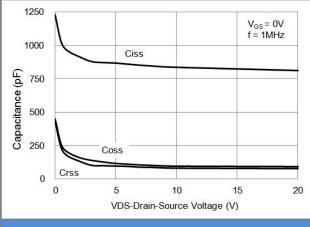
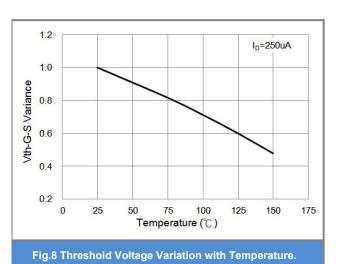


Fig.9 Capacitance vs. Drain-Source Voltage.

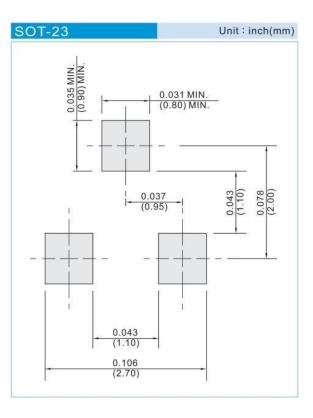




#### PART NO PACKING CODE VERSION

PART NO PACKING CODE	Package Type	Packing type	Marking	Version
CSM212N6S23E	SOT-23	3K pcs / 7" reel		Halogen free

#### MOUNTING PAD LAYOUT





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